

MR1035-820

IN THE CLAIMS:

Please cancel Claims 5-8 and 16-19 without prejudice or disclaimer of the subject matter thereof.

Please replace Claims 1 and 9 with the “clean copy” of the amended Claims 1 and 9:

CLEAN COPY OF AMENDED CLAIMS:

*mwD* 7  
1. (Thrice Amended) A planarization method of inter-layer dielectrics,  
comprising the steps of:

providing a semiconductor substrate including a field oxide, a  
source, a drain, and a gate formed thereon;

*C1*  
forming a dielectric layer used as an inter-layer dielectric on said  
semiconductor substrate, lapping said dielectric layer by means of a chemical mechanical  
polishing; and

forming on said lapped dielectric layer a cap layer of a refractive  
index larger than 1.6, wherein said cap layer is a silicon nitrogen-oxide layer translucent  
to ultra-violet light.

*mwD*  
9. (Thrice Amended) A planarization method of inter-metal dielectrics,  
comprising the steps of:

*C2*  
providing a semiconductor substrate having a plurality of metal-  
interconnects formed thereon;

forming a dielectric layer used as an inter-metal dielectric on said  
substrate, lapping said dielectric layer by means of a chemical mechanical polishing; and

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forming on said lapped dielectric layer a cap layer of a refractive index larger than 1.6, wherein said cap layer is a silicon nitrogen-oxide layer translucent to ultra-violet light.

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